

# HA13566AF

Combo (Spindle & VCM) Driver

**HITACHI**

ADE-207-250 (Z)

1st Edition

December 1997

## Description

The HA13566AF is combination of Spindle and VCM Driver designed for HDD and have following functions and features.

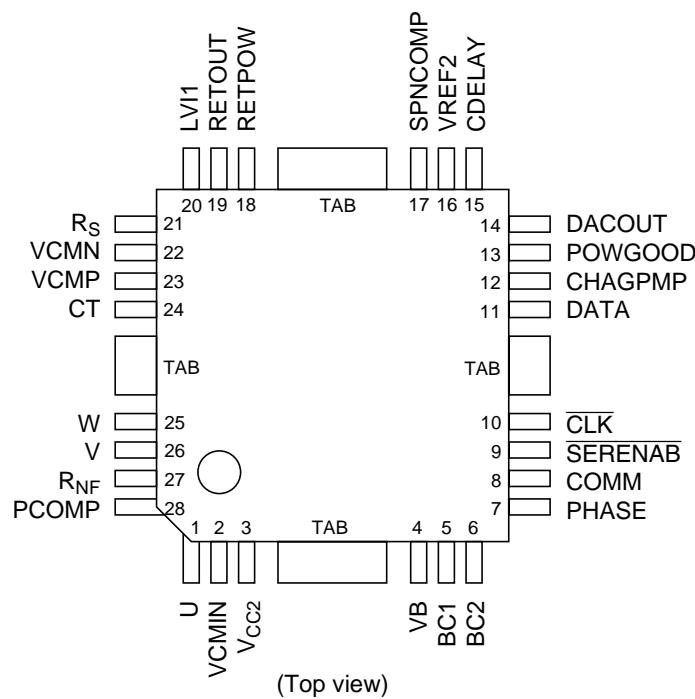
## Functions

- 1.0 A max/3-phase spindle motor driver
- 400 mA max VCM driver
- 100 mA max retract driver
- 11 bit serial interface
- 9 bit DAC for VCM control
- Commutation logic for sensor-less motor
- Center tap pull-up driver for half wave driver
- Soft switching matrix
- Charge pump
- Booster
- Power monitor
- OTSD

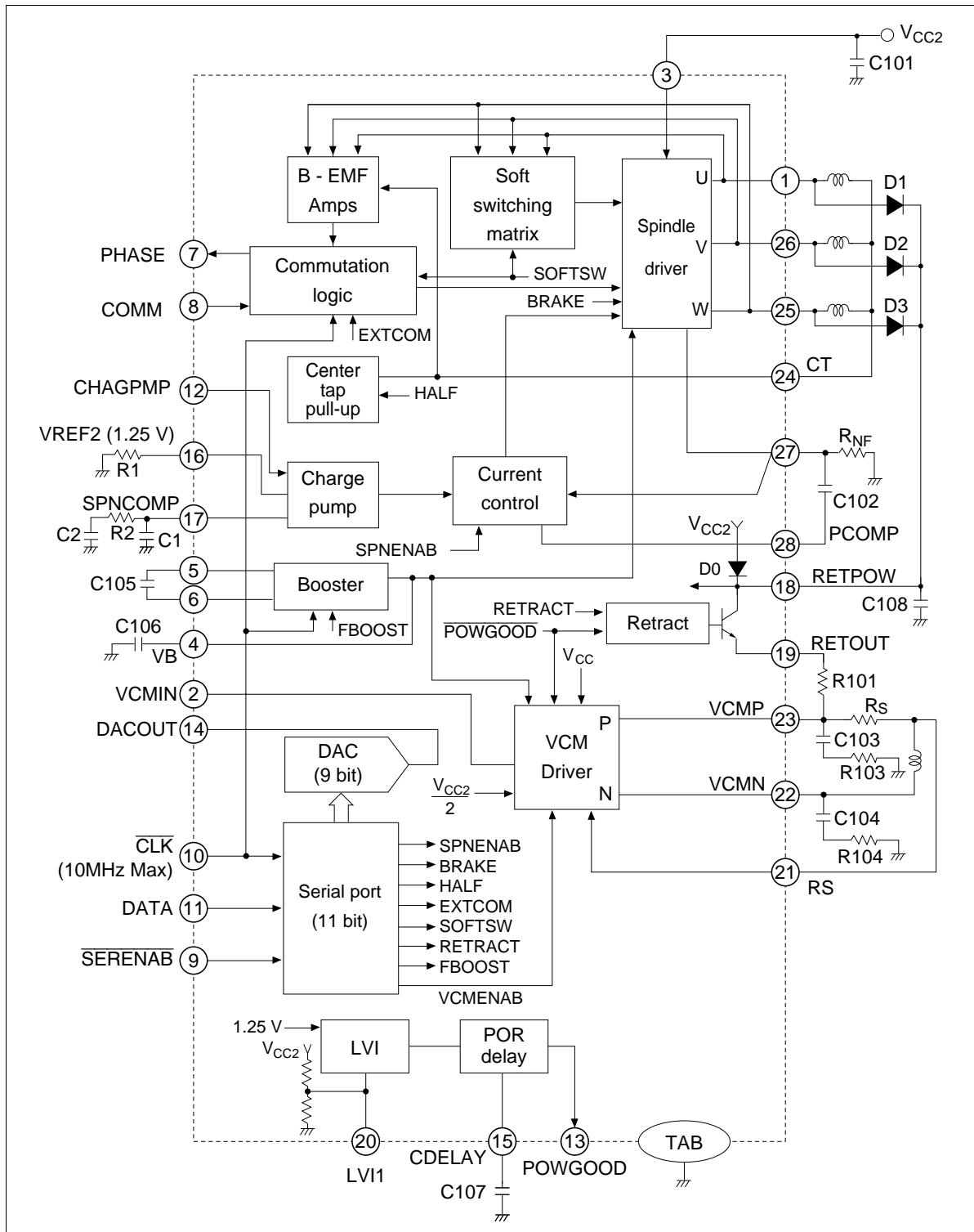
## Features

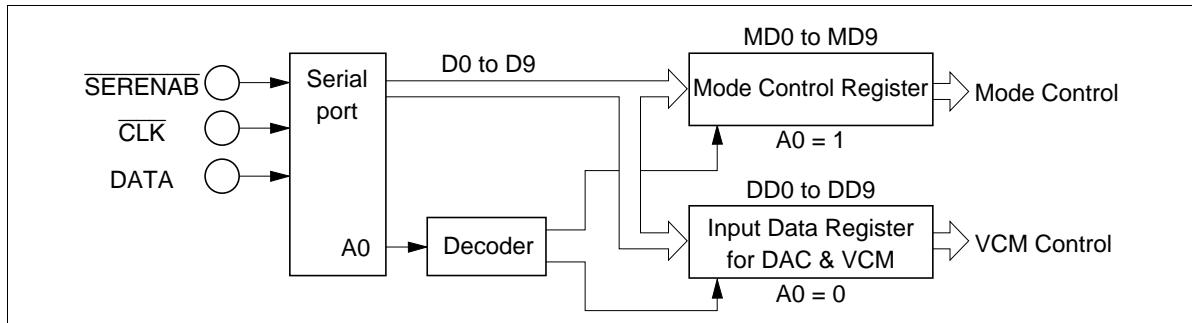
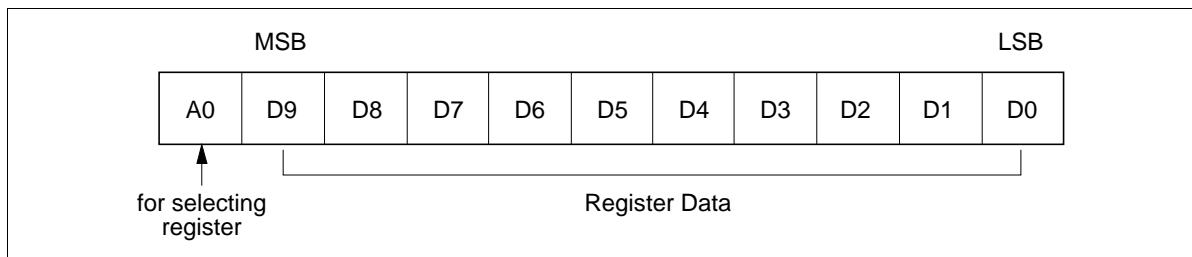
- Low output saturation voltage  
Spindle driver      1.0 V typ (@0.8 A)  
                        0.2 V typ (@0.1 A)
- VCM driver      1.0 V typ (@400 mA)
- Soft switching drive
- Minimum surface mount package  
body size 7 × 7 mm

## Pin Arrangement



## Block Diagram



**Serial Port****Construction****Figure 1 Serial Port****Data construction****Input Data Construction****Figure 2 Input Data (1)**

The serial port is required the 11 bit data (D0 to D9 and A0). Address bit A0 is used to select the register as follows. When the data length is less than 11 bits, the internal register will not be up dated. And when the data length is more than 11 bits, this register will take late 10 bits and ignore the faster bit.

<b>A0</b>	<b>Register</b>
0	Input data register of DAC & VCMGAIN
1	Mode control register

## Mode Control Register (A0 = 1)

Bit	Symbol	1	0	Note
MD0	SPNENAB	Spindle enable	Spindle disable	1
MD1	BRAKE	Brake enable	Brake disable	1
MD2	Not use	—	—	
MD3	HALF	Half wave drive	Full wave drive	
MD4	EXTCOM	External commutation	Internal commutation	2
MD5	SOFTSW	Soft switching	Switching	
MD6	VCMENAB	VCM enable	VCM disable	
MD7	RETRACT	Retracting	Not retracting	
MD8	POLESEL	for 12 poles motor	for 8 poles motor	3
MD9	FBOOST	Low frequency	High frequency	4

- Notes:
1. The spindle motor is independently winding to the value of the MD2, during the MD1 is true.
  2. The bit MD4 select a commutation mode at driving by B-EMF sensing. (See Commutation timing)
  3. In order to prevent the misdetection of back-EMF amplifier, the bit MD8 should be chosen as shown above table.
  4. The bit MD9 determine the operating frequency of Booster Circuit. According to the frequency of Input CLK at pin 10, the value of MD9 should be chosen as shown below.

CLK (at pin 10)	MD9
7.1 MHz to 10 MHz	0
4.0 MHz to 7.0 MHz	1

## Input Data Register (A0 = 0)

Bit / DD0 to DD9: These input data are used to control the output current at VCM driver as shown follows.

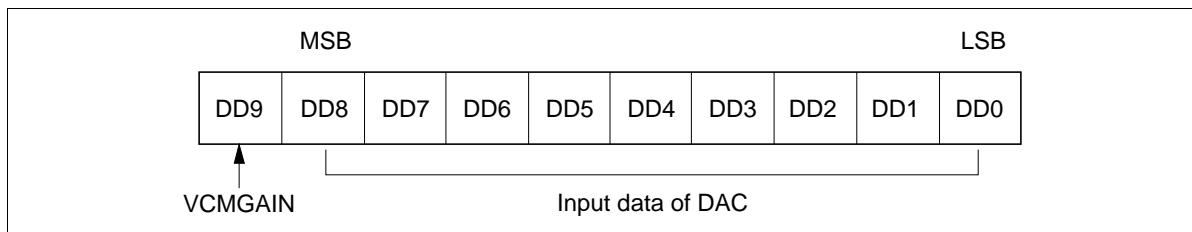


Figure 3 Input Data (2)

The data bit DD9 determine the transfer gain  $G_{VCM}$  which is specified as the relationship between the input data at the input data register and the output current at VCM amplifier. (See the under table)

DD9	DATA	$I_o$ [mA]
1	1FF	$+199.2/R_s$
1	100	0.000
1	000	$-200.0/R_s$
0	1FF	$+24.9/R_s$
0	100	0.000
0	000	$-25.0/R_s$

## Data Input Timing

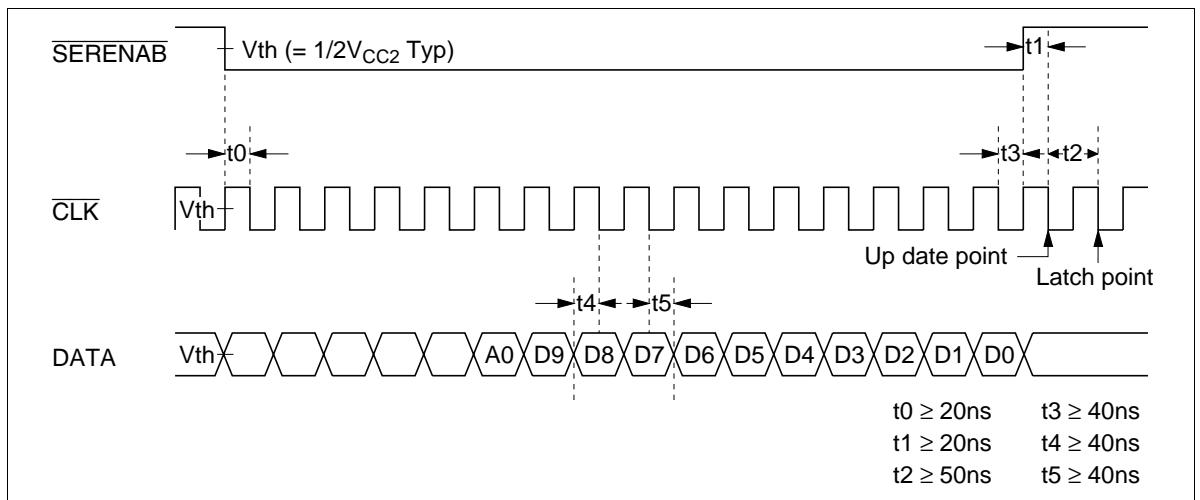


Figure 4 Input Timing on Serial Port

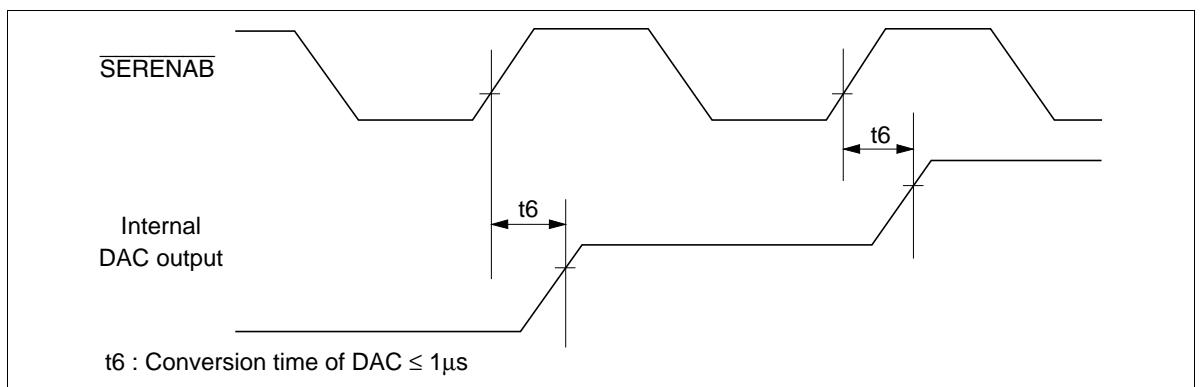
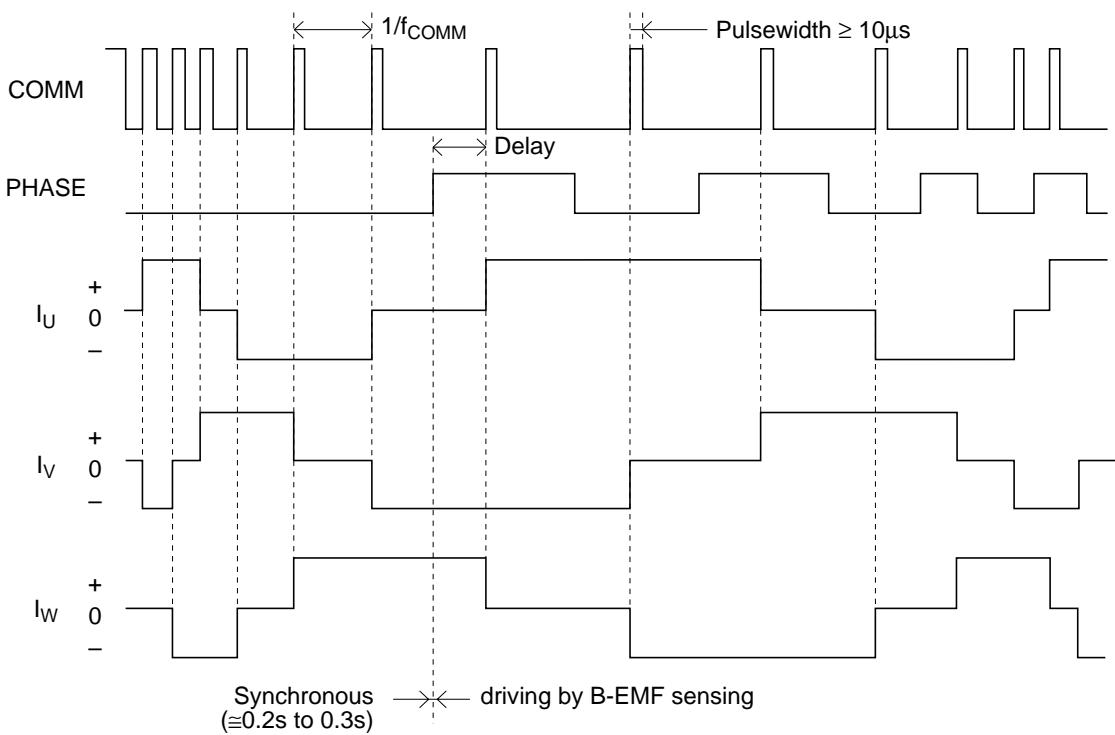


Figure 5 Conversion Timing on DAC

## Commutation Timing

### Commutation for starting up



Note: 1. The frequency of COMM signal  $f_{COMM}$  can be designed as follows.

$$f_{COMM \text{ (max)}} = 2.5 \sqrt{\frac{P \cdot K_T \cdot I_0}{J}} \quad (\text{Hz}) \quad \text{(for begin of synchronous driving)} \quad (1)$$

$$f_{COMM \text{ (min)}} = 0.5 \sqrt{\frac{P \cdot K_T \cdot I_0}{J}} \quad (\text{Hz}) \quad \text{(for end of synchronous driving)} \quad (2)$$

Where,

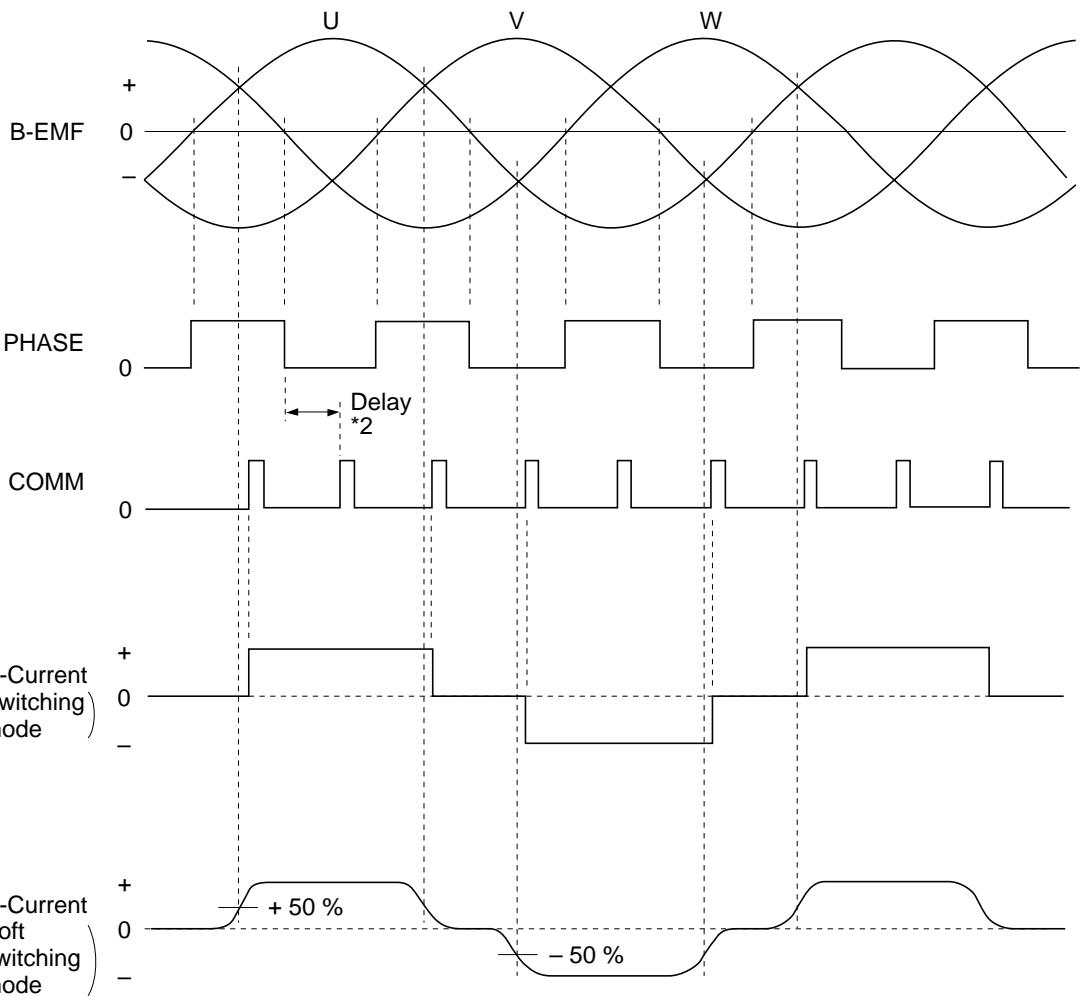
P : Pole number of spindle motor (Hz)

$K_T$  : Torque constant (kg · cm/A)

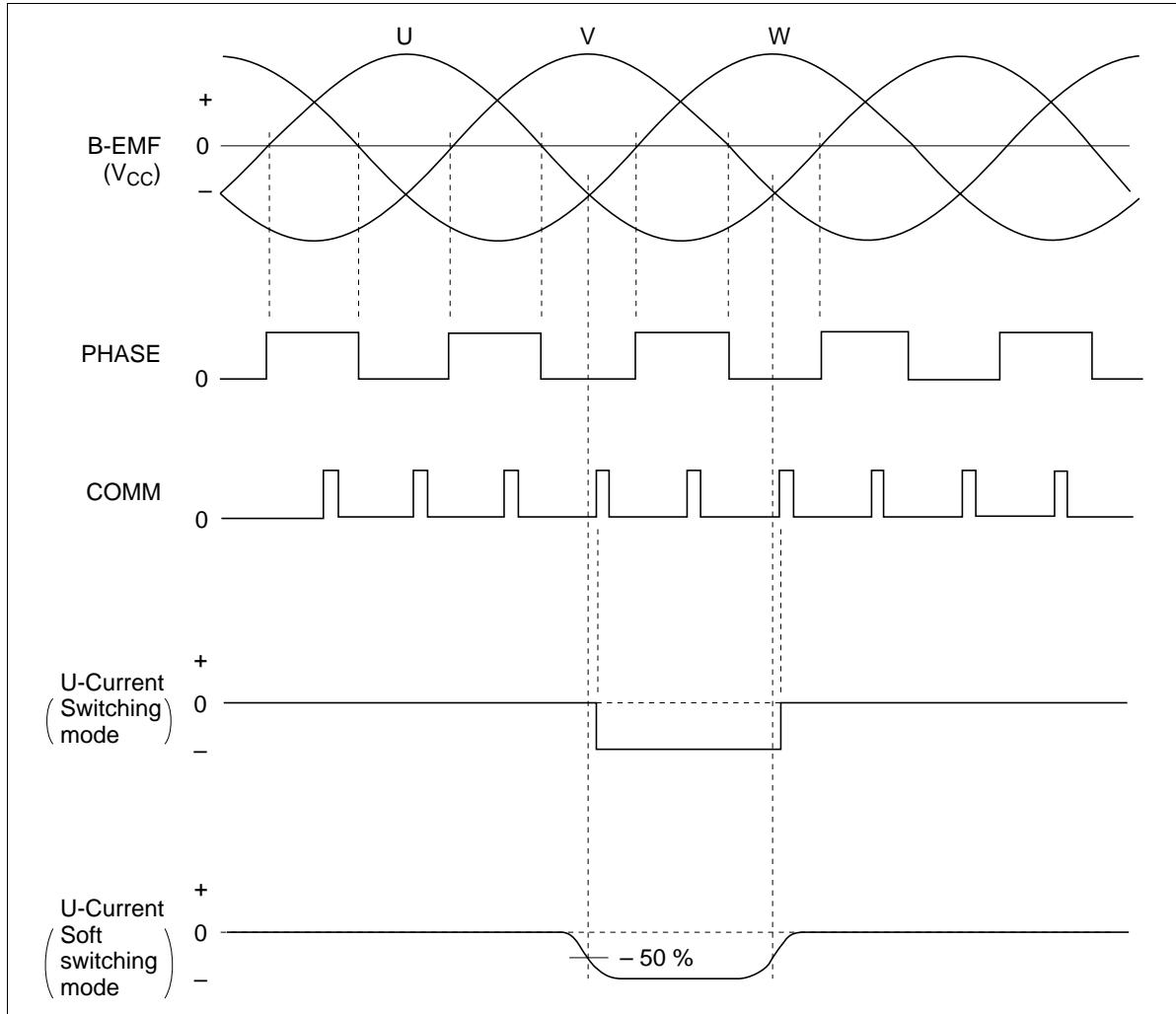
$I_0$  : Start up current (A)

J : Moment of inertia (kg · cm · S<sup>2</sup>)

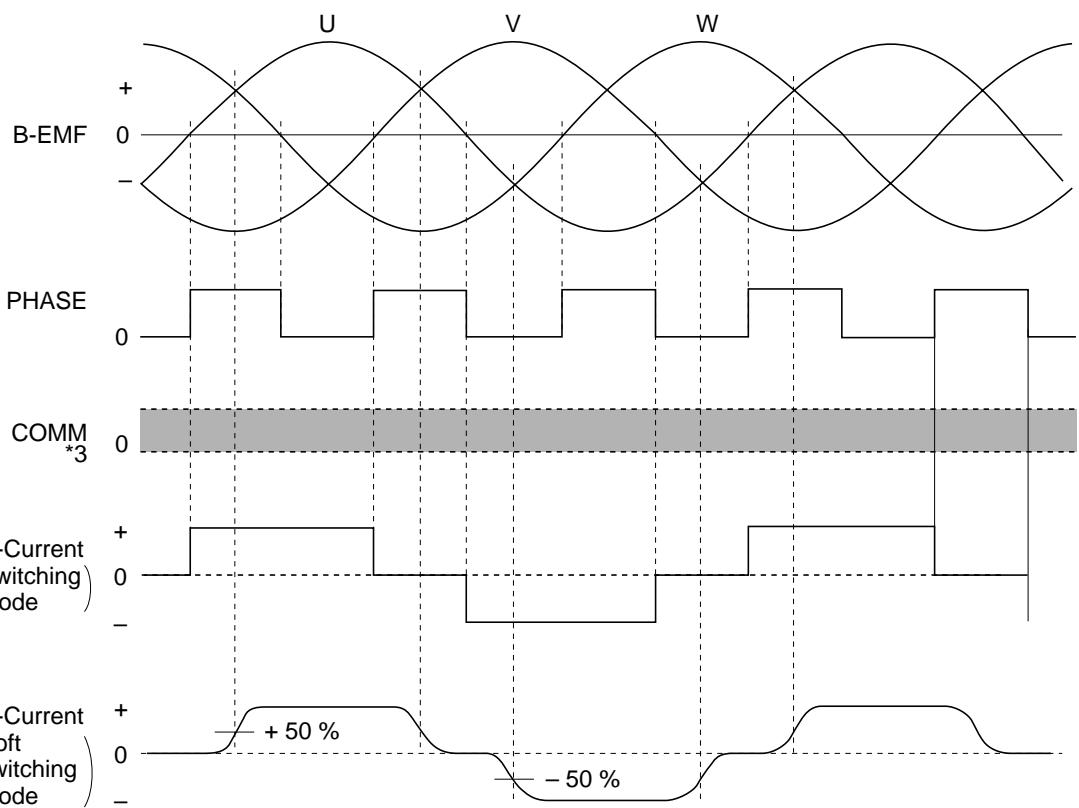
## External Commutation Mode (Full Wave Drive)



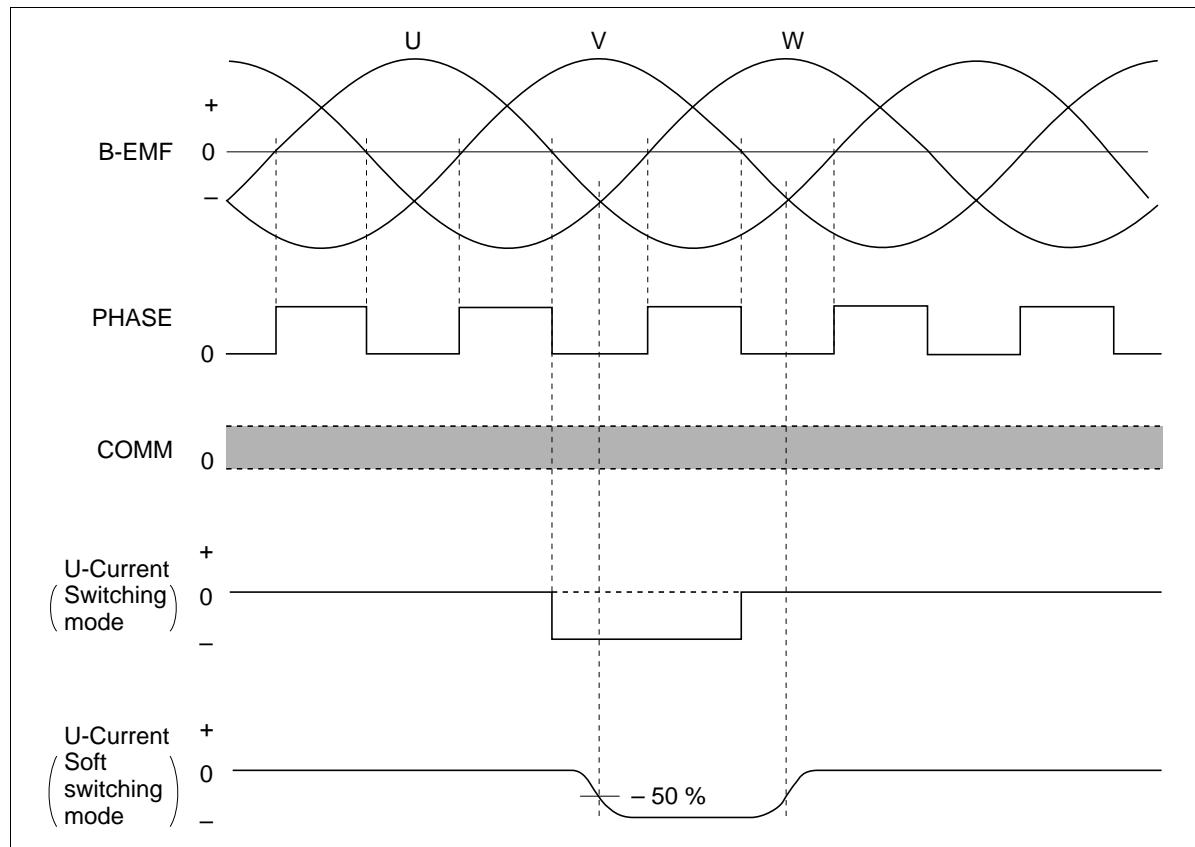
Note: 2. Provided by MPU.

**External Commutation Mode (Half Wave Mode)**

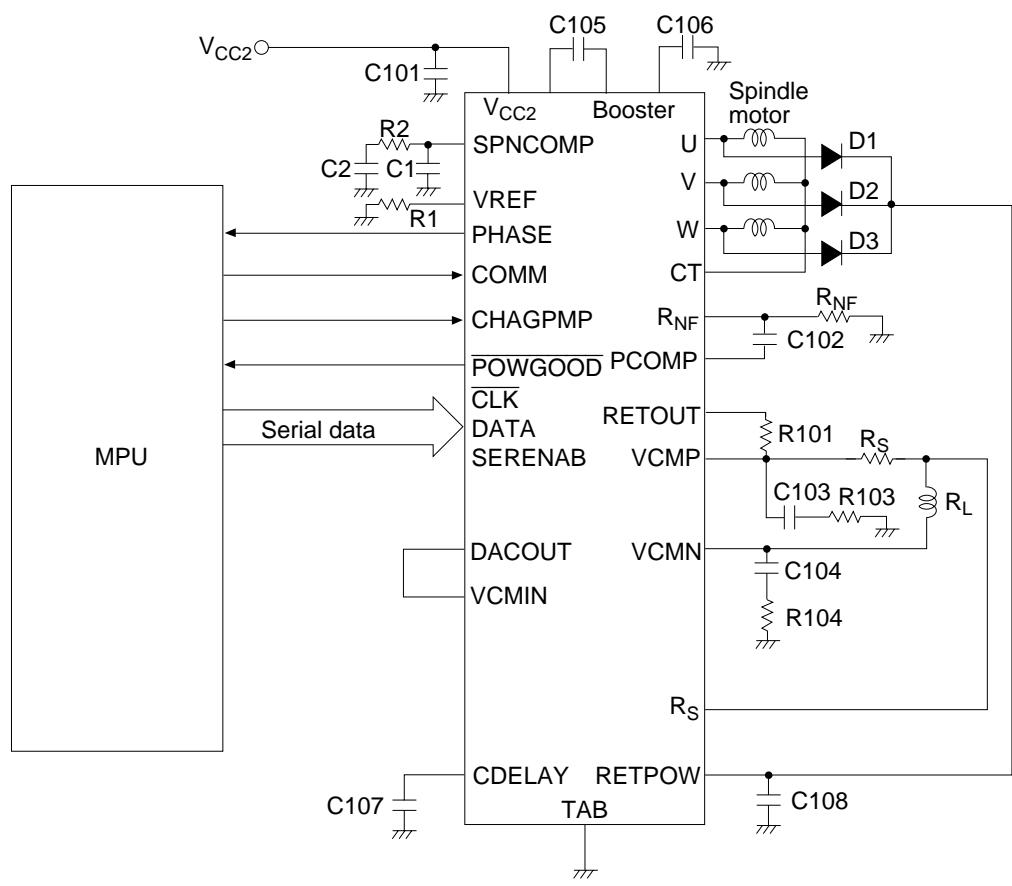
## Internal Commutation Mode (Full Wave Mode)



Note: 3. When the internal commutation mode is selected, the commutation of the motor is automatically selected at the B-EMF sensing drive. But don't open the COMM terminal.

**Internal Commutation Mode (Half Wave Mode)**

## Application



## External Component

Parts No.	Recommended Value	Purpose	Notes
R <sub>1</sub>	≤ 47 kΩ	Integral constant	1
R <sub>2</sub>	—	Integral constant	1
R <sub>101</sub>	—	Set retract current	2
R <sub>103</sub> , R <sub>104</sub>	2.2 Ω	For stability	
R <sub>NF</sub>	≥ 0.2 Ω	Spindle current sense	3
R <sub>S</sub>	0.47 Ω	VCM current sense	
C <sub>1</sub> , C <sub>2</sub>	—	Integral constant	1
C <sub>101</sub>	0.1 μF	Power supply bypass	
C <sub>102</sub>	0.1 μF	Phase compensation for spindle driver	
C <sub>103</sub> , C <sub>104</sub>	0.1 μF	For stability	
C <sub>105</sub>	0.47 μF	For booster	
C <sub>106</sub>	4.7 μF	For booster	
C <sub>107</sub>	—	POR delay	4
C <sub>108</sub>	—	Retpower filter	
D1, D2, D3	—	For retract	

Notes: 1. This integral constants can be designed as follows.

$$\omega_0 = \frac{2\pi N_o}{600} \quad (3)$$

$$\frac{R_2}{R_1} = \frac{J \omega_0 N_o R_{NF}}{9.55 Kt Gctl Vref2} \quad (4)$$

$$C_1 = \frac{1}{\sqrt{10} \omega_0 R_2} \quad (5)$$

$$C_2 = 10C_1 \quad (6)$$

Where,

$\omega_0$  = Time constant of servo loop

N<sub>o</sub> = Rotation number (rpm)

J = Moment of inertia (kg cm•s<sup>2</sup>)

R<sub>NF</sub> = Current sense resistor (Ω)

Gctl = Control gain (see electrical characteristics)

Vref2 = Internal reference voltage (See electrical characteristics)

2. The retract current is determined as follows.

$$I_{ret} = \frac{V_{ret\text{pow}} - V_{satret}}{R_{101} + R_L + R_S} \quad (7)$$

where,

$R_L$  = VCM coil Resistor.

$V_{satret}$  = Retout saturation voltage (See electrical characteristics)

3. The motor start up current  $I_O$  is determined as follows.

$$I_O = \frac{V_{ref1}}{R_{NF}} \quad (A) \quad (8)$$

Where,  $V_{ref1}$  = Current limiter reference voltage

(See electrical characteristics)

4. The power on reset delay time is determined as follows.

$$t_{POR} = 10^5 \cdot C_{107} \quad (\text{See electrical characteristics}) \quad (9)$$

**Absolute Maximum Ratings (Ta = 25°C)**

Item	Symbol	Value	Units	Notes
Power supply voltage	V <sub>CC2</sub>	7.0	V	1
Spindle current	I <sub>SPN</sub>	1.0	A	2
VCM current	I <sub>VCM</sub>	400	mA	2
Retract current	I <sub>RET</sub>	100	mA	2
Input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V	
Power dissipation (Ta = 65°C)	P <sub>T1</sub>	1.0	W	3
Power dissipation (Tc = 100°C)	P <sub>T2</sub>	2.0	W	3
Junction temperature	T <sub>j</sub>	150	°C	4
Storage temperature range	T <sub>STG</sub>	-55 to +125	°C	

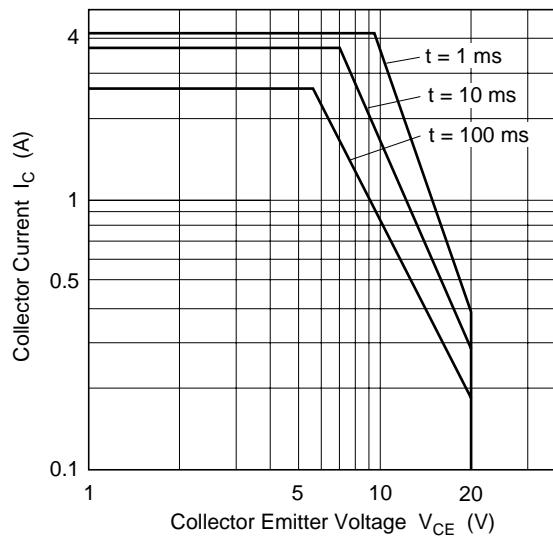
Notes: 1. Operating voltage range is 4.25 V to 5.75 V.

2. ASO of each output transistor is shown below. Operating locus must be within the ASO.
3. Thermal resistance is shown below.

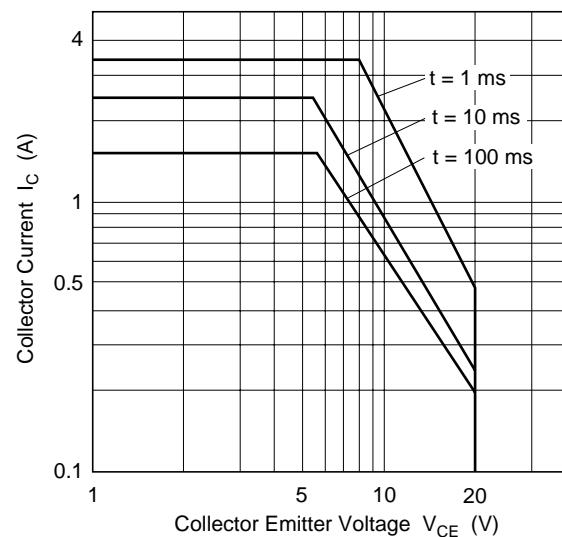
$$\theta_{j-c} \leq 25^\circ\text{C/W}$$

$$\theta_{j-a} \leq 80^\circ\text{C/W}$$

4. Operating junction temperature range is 0 to +125°C.



**Figure 6 ASO of Output Transistor (Spindle Driver)**



**Figure 7 ASO of Output Transistor (VCM Driver)**

**Electrical Characteristics (Ta = 25°C, V<sub>CC</sub> = 5 V)**

Item	Symbol	Min	Typ	Max	Units	Test Conditions	Applicable Terminal	Note
Supply current	I <sub>CC1</sub>	—	15	20	mA	Enable mode	3	
Logic input	Input low current	I <sub>IL</sub>	—	0	±10	µA	V <sub>IL</sub> =0V	8, 9, 10, 11
	Input high current	I <sub>IH</sub>	—	—	±10	µA	V <sub>IH</sub> =5V	
	Input low voltage	V <sub>IL</sub>	—	—	1.5	V		
	Input high voltage	V <sub>IH</sub>	3.5	—	—	V		
	Clock frequency	f <sub>CLK</sub>	—	—	10	MHz		
Logic output	Output high voltage	V <sub>OH</sub>	4.4	—	—	V	I <sub>OH</sub> =1mA	7, 13
	Output low voltage	V <sub>OL</sub>	—	—	0.4	V	I <sub>OL</sub> =1mA	
Spindle driver	Total saturation voltage	V <sub>satspn</sub>	—	1.0	1.4	V	I <sub>spn</sub> =0.8A	1, 25, 26
	—	—	0.2	0.3	V	I <sub>spn</sub> =100mA		
	Output leak current	Icer1	—	—	5	mA	M3D=1, V <sub>O</sub> =V <sub>CC</sub> +3V	
	Current limiter reference voltage	Vref1	139	155	171	mV	R <sub>NF</sub> =1.0Ω	
B-EMF amps	Current control gain	Gctl	-14	-12	-10	dB		
	Input sensitivity	Vmin	—	50	—	mVp-p		1, 25, 26
Charge pump	Input high voltage	V <sub>IHCp</sub>	3.5	—	—	V		12
	Input low voltage	V <sub>ILCP</sub>	—	—	1.5	V		
	Input high current	I <sub>IHCp</sub>	—	150	200	µA	V <sub>IHCp</sub> =5V	
	Input dead current	I <sub>IDCP</sub>	—	—	±10	µA		
	Input low current	I <sub>ILCP</sub>	—	-150	-200	µA	V <sub>ILCP</sub> =0V	
	Output current	Charge current	+44	+54	+64	µA	R1=24kΩ	17
	Discharge current	—	-64	-54	-44	µA	R1=24kΩ	
	Output cutoff current	Ioff	—	—	±50	nA		
VCM driver	Reference voltage	Vref2	1.32	1.39	1.46	V	R1=24kΩ	16
	VCM input resistor	Rin	42	60	78	kΩ		2
	Output quiescent voltage	Vq	V <sub>CC2</sub> /2	V <sub>CC2</sub> /2 +5%	V <sub>CC2</sub> /2 +10%	V		22, 23
	Output leak current	Icer2	—	—	±5	mA		
	Total output saturation voltage	V <sub>satvcm</sub>	—	1.0	1.35	V	I <sub>vcm</sub> =400mA	
		—	0.8	1.0	V	I <sub>vcm</sub> =200mA		

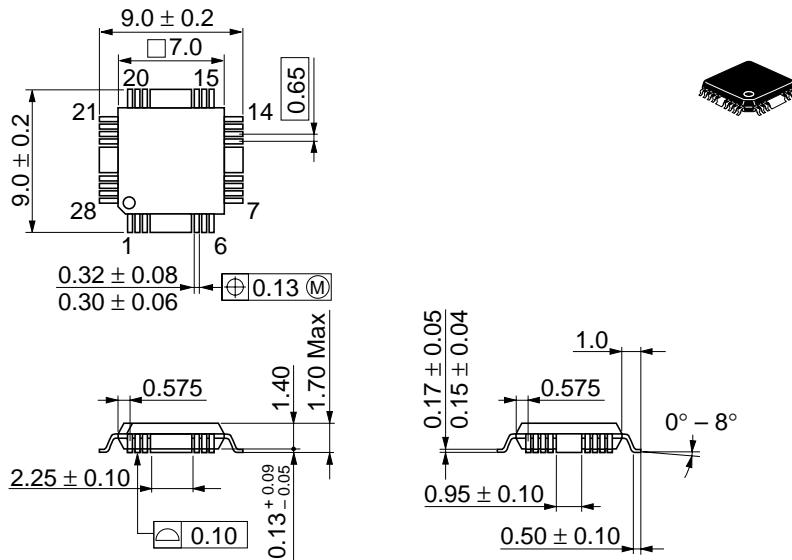
## Electrical Characteristics (Ta = 25°C, V<sub>CC</sub> = 5 V) (cont)

Item		Symbol	Min	Typ	Max	Units	Test Conditions	Applicable Terminal	Note
VCM driver	Resolution	I <sub>RES</sub>	—	1/512	—	—		21, 22, 23	1
	DAC output resistor	R <sub>OUT</sub>	—	—	50	Ω		14	
	Output current full scale	I <sub>FS1</sub>	345	385	425	mA	DD9=1, R <sub>S</sub> =1Ω, R <sub>L</sub> =14Ω	2, 14	2
		I <sub>FS2</sub>	45	50	55	mA			
	Gain ratio	I <sub>FS1</sub> / I <sub>FS2</sub>	7.5	8.0	8.5	—			
	Offset	I <sub>OFF1</sub>	—	—	±15	LSB	DD9=1, R <sub>S</sub> =1Ω, R <sub>L</sub> =14Ω	21, 22, 23	
		I <sub>OFF2</sub>	—	—	±20	LSB			
		I <sub>OFF3</sub>	—	—	±80	LSB	I <sub>OFF1</sub> ×8-I <sub>OFF2</sub>		
	Linearity	I <sub>LIN</sub>	—	—	±1	LSB			
	Gain Bandwidth	B	—	40	—	kHz	DD9=1, R <sub>S</sub> =1Ω, R <sub>L</sub> =14Ω		1
			—	95	—	kHz	DD9=0, R <sub>S</sub> =1Ω, R <sub>L</sub> =14Ω		
Retract driver	Retpow voltage	V <sub>RETPOW</sub>	1.4	—	—	V	R <sub>S</sub> =1.0Ω, R <sub>L</sub> =14Ω I <sub>RET</sub> =100mA	18	
	Retout saturation voltage	V <sub>SATRET</sub>	—	1.0	1.2	V	I <sub>RET</sub> =100mA	19	
LVI	Operating voltage	V <sub>SD</sub>	3.55	3.85	4.15	V		3	
	Recovery voltage	V <sub>REC</sub>	3.9	4.2	4.5	V			1
POR	Power on reset delay time	POR	5	10	20	ms	C <sub>107</sub> =0.1μF	13	
OTSD	Operating temperature	T <sub>SD</sub>	125	150	—	°C			1
	Hysteresis	Thys	—	25	—	°C			

- Note:
1. Design guide only
  2. Specified by shorting between VCMIN and DACOUT.

## Package Dimensions

Unit: mm



Dimension including the plating thickness  
Base material dimension

Hitachi Code	FP-28T
JEDEC	—
EIAJ	—
Weight (reference value)	0.2 g

## Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

# HITACHI

### Hitachi, Ltd.

Semiconductor & Integrated Circuits.

Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan  
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: <a href="http://semiconductor.hitachi.com/">http://semiconductor.hitachi.com/</a>
	Europe	: <a href="http://www.hitachi-eu.com/hel/ecg">http://www.hitachi-eu.com/hel/ecg</a>
	Asia (Singapore)	: <a href="http://www.has.hitachi.com.sg/grp3/sicd/index.htm">http://www.has.hitachi.com.sg/grp3/sicd/index.htm</a>
	Asia (Taiwan)	: <a href="http://www.hitachi.com.tw/E/Product/SICD_Frame.htm">http://www.hitachi.com.tw/E/Product/SICD_Frame.htm</a>
	Asia (HongKong)	: <a href="http://www.hitachi.com.hk/eng/bo/grp3/index.htm">http://www.hitachi.com.hk/eng/bo/grp3/index.htm</a>
	Japan	: <a href="http://www.hitachi.co.jp/Sicd/indx.htm">http://www.hitachi.co.jp/Sicd/indx.htm</a>

### For further information write to:

Hitachi Semiconductor (America) Inc.  
179 East Tasman Drive,  
San Jose, CA 95134  
Tel: <1> (408) 433-1990  
Fax: <1>(408) 433-0223

Hitachi Europe GmbH  
Electronic Components Group  
Dornacher Straße 3  
D-85622 Feldkirchen, Munich  
Germany  
Tel: <49> (89) 9 9180-0  
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.  
Electronic Components Group.  
Whitebrook Park  
Lower Cookham Road  
Maidenhead  
Berkshire SL6 8YA, United Kingdom  
Tel: <44> (1628) 585000  
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.  
16 Collyer Quay #20-00  
Hitachi Tower  
Singapore 049318  
Tel: 535-2100  
Fax: 535-1533

Hitachi Asia Ltd.  
Taipei Branch Office  
3F, Hung Kuo Building, No.167,  
Tun-Hwa North Road, Taipei (105)  
Tel: <886> (2) 2718-3666  
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.  
Group III (Electronic Components)  
7/F., North Tower, World Finance Centre,  
Harbour City, Canton Road, Tsim Sha Tsui,  
Kowloon, Hong Kong  
Tel: <852> (2) 735 9218  
Fax: <852> (2) 730 0281  
Telex: 40815 HITEC HX